

A Comparative Study: the structural and optoelectronic properties of Al- and Ga-doped ZnO films deposited by atmospheric pressure plasma jet

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Fig. 1. XRD patterns of (a) GZO and (b) AZO films deposited with different parameters. The area ratio of the peaks of (c) GZO and (d) AZO films with different deposition parameters.

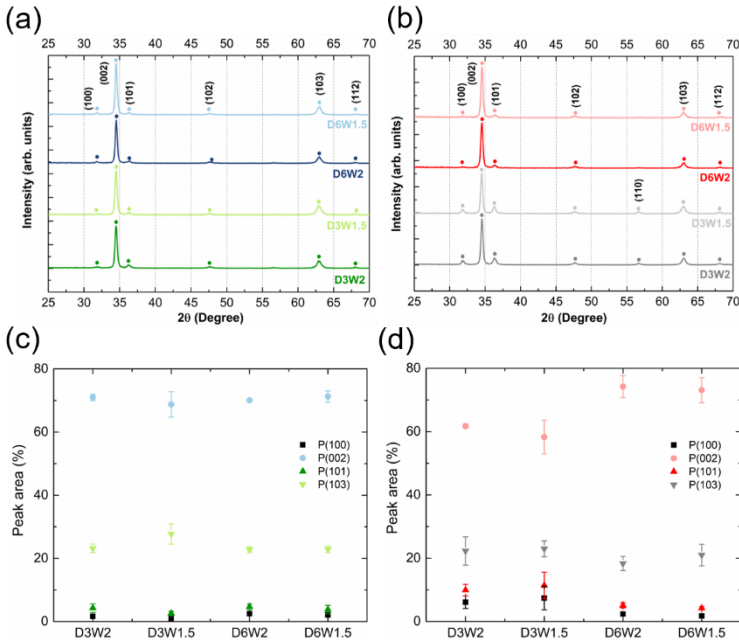


Fig. 2. SEM images of the samples' top views deposited with different deposition parameters: (a) GZO-D3W2 (b) GZO-D3W1.5 (c) GZO-D6W2 (d) GZO-D6W1.5 (e) AZO-D3W2 (f) AZO-D3W1.5 (g) AZO-D6W2 (h) AZO-D6W1.5

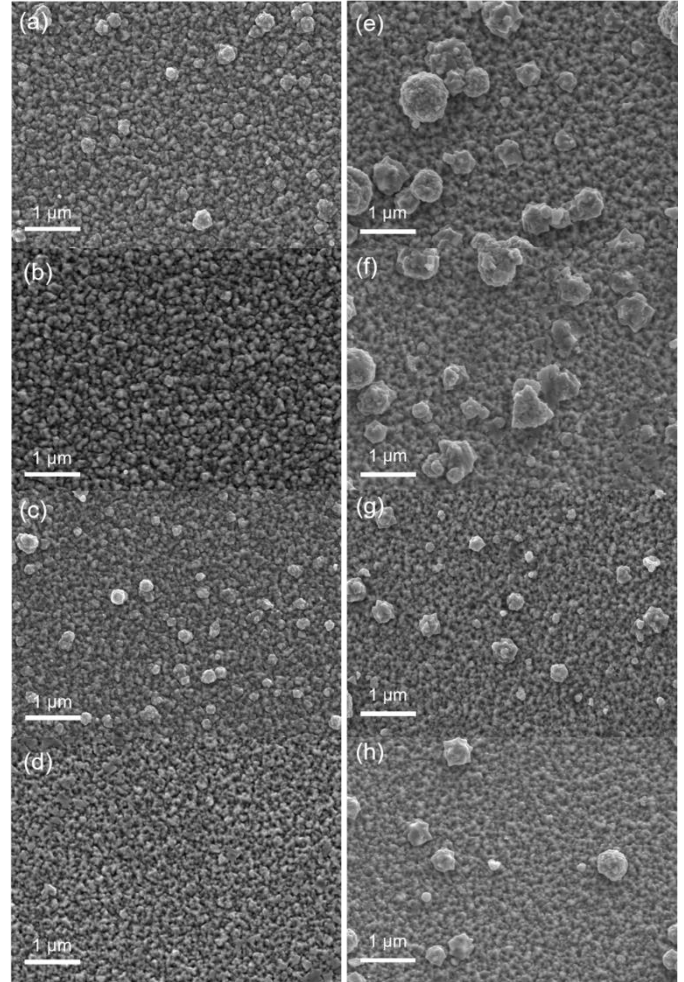


Fig. 3. Hall measurement of (a) GZO films and (b) AZO films with different deposition parameters.

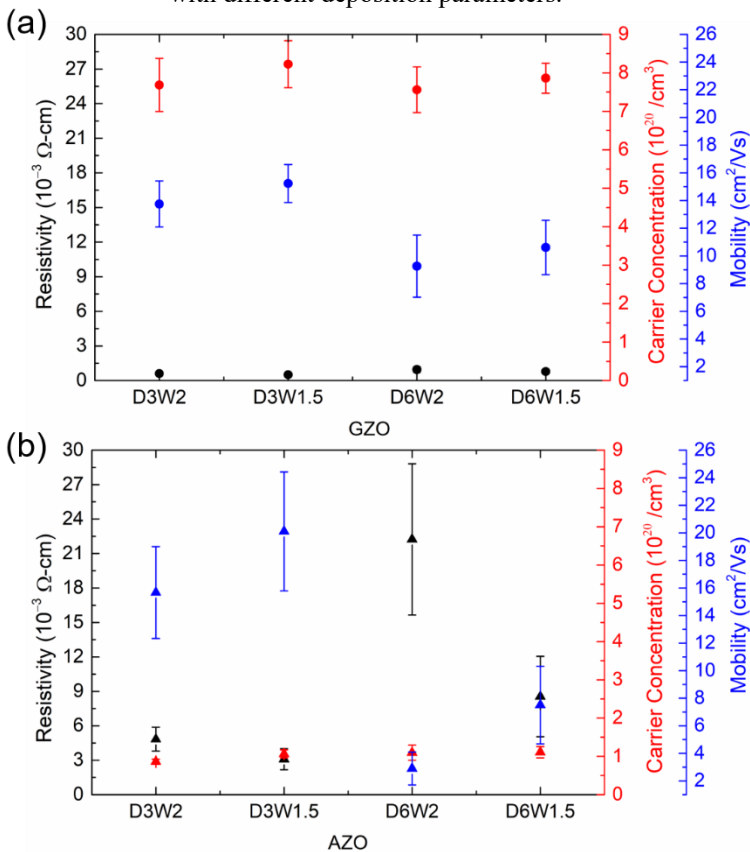


Fig. 4. Total transmittance of GZO and AZO films with different deposition parameters.

